

**PRELIMINARY**

Notice: This is not a final specification.  
Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR <GaAs FET>

# MGFC42V4450A

**4.4~5.0GHz BAND 16W INTERNALLY MATCHED GaAs FET**

## DESCRIPTION

The MGFC42V4450A is an internally impedance-matched GaAs power FET especially designed for use in 4.4~5.0 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

## FEATURES

- Class A operation
- Internally matched to 50Ω system
- High output power  
 $P_{1dB} = 18\text{ W (TYP) @ 4.4~5.0 GHz}$
- High power gain  
 $G_{LP} = 9\text{ dB (TYP) @ 4.4~5.0 GHz}$
- High power added efficiency  
 $\eta_{add} = 33\% \text{ (TYP) @ 4.4~5.0 GHz, } P_{1dB}$
- Hermetically sealed metal-ceramic package
- Low distortion [Item: -51]  
 $IM_3 = -45\text{ dBc (TYP) @ } P_o = 31\text{ (dBm) S.C.L.}$
- Low thermal resistance  $R_{th(ch-c)} \leq 1.6\text{ (}^\circ\text{C/W)}$

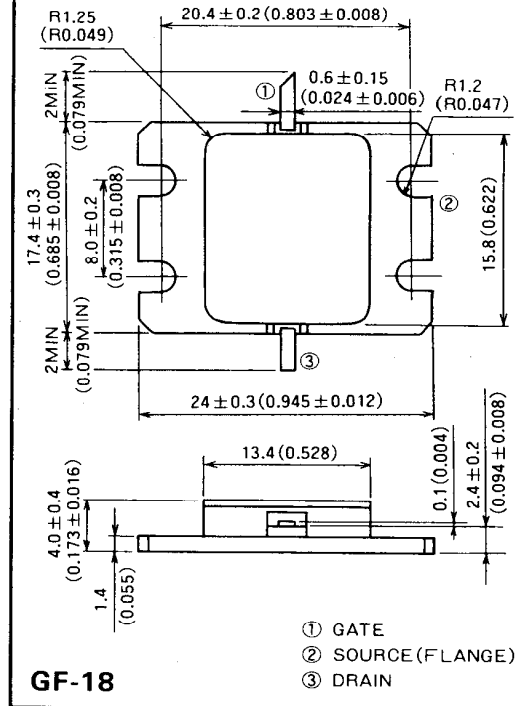
## APPLICATION

- Item-01: 4.4~5.0 GHz band power amplifiers.
- Item-51: Digital radio communication

## QUALITY GRADE

- IG

## OUTLINE DRAWING Unit: millimeters (inches)



## ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Symbol	Parameter	Ratings	Unit
V <sub>GD0</sub>	Gate to drain voltage	-15	V
V <sub>GS0</sub>	Gate to source voltage	-15	V
I <sub>D</sub>	Drain current	12	A
I <sub>GR</sub>	Reverse gate current	-40	mA
I <sub>GF</sub>	Forward gate current	+84	mA
P <sub>T</sub>	Total power dissipation *1	93.7	W
T <sub>ch</sub>	Channel temperature	175	°C
T <sub>stg</sub>	Storage temperature	-65 ~ +175	°C

\*1: T<sub>c</sub> = 25°C

## RECOMMENDED BIAS CONDITIONS

- V<sub>DS</sub> = 10V
- I<sub>D</sub> = 4.5A
- R<sub>g</sub> = 25Ω
- Refer to Bias Procedure

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
I <sub>DSS</sub>	Saturated drain current	V <sub>DS</sub> = 3V, V <sub>GS</sub> = 0V	—	9	12	A
g <sub>m</sub>	Transconductance	V <sub>DS</sub> = 3V, I <sub>D</sub> = 4.4A	—	4	—	S
V <sub>GS(off)</sub>	Gate to source cut-off voltage	V <sub>DS</sub> = 3V, I <sub>D</sub> = 80mA	-2	-3	-4	V
P <sub>1dB</sub>	Output power at 1dB gain compression	V <sub>DS</sub> = 10V, I <sub>D</sub> = 4.5A, f = 3.7~4.2GHz	41.5	42.5	—	dBm
G <sub>LP</sub>	Linear power gain		8	9	—	dB
I <sub>D</sub>	Drain current		—	4.5	—	A
η <sub>add</sub>	Power added efficiency		—	33	—	%
IM <sub>3</sub>	3rd order IM distortion *1		-42	-45	—	dBc
R <sub>th(ch-c)</sub>	Thermal resistance *2		ΔV <sub>f</sub> method	—	—	1.6

\*1: Item-51, 2-tone test P<sub>o</sub> = 31dBm Single Carrier Level f = 5.0 Δf = 10MHz. \*2: Channel to case

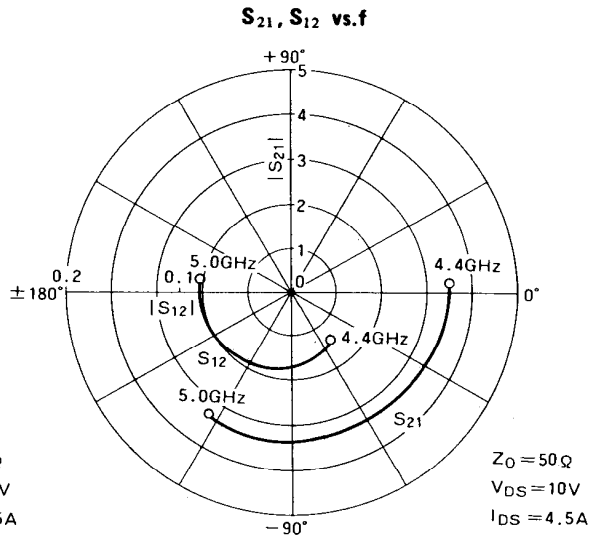
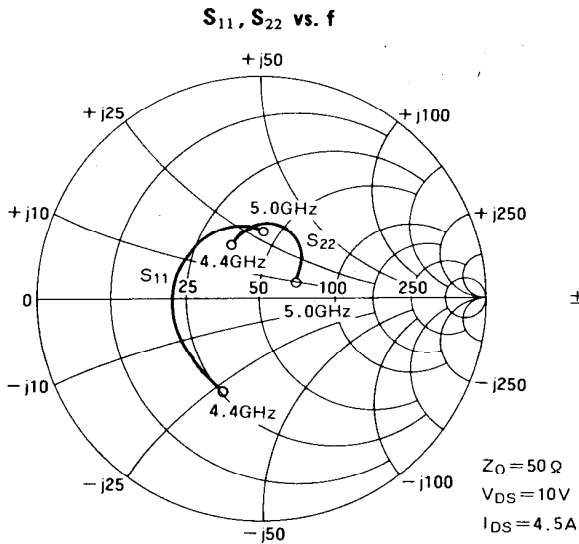
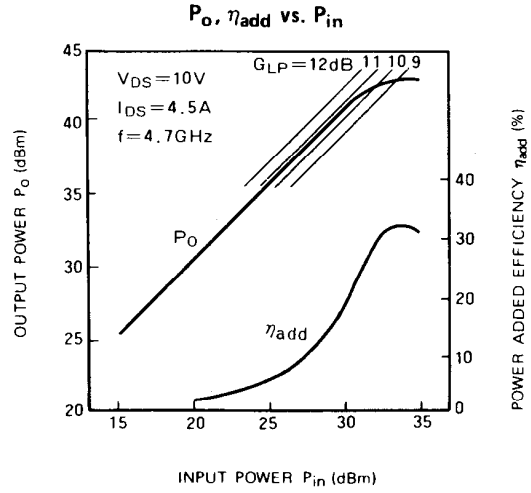
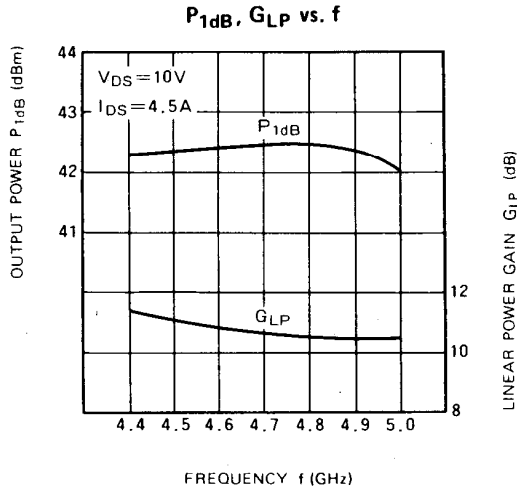
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**TYPICAL CHARACTERISTICS (Ta=25°C)**



**S PARAMETERS (Ta=25°C, VDS=10V, IDS=4.5A)**

f (GHz)	S Parameters (TYP.)							
	$S_{11}$		$S_{21}$		$S_{12}$		$S_{22}$	
	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)
4.4	0.46	-113	3.63	3	0.054	-49	0.31	121
4.5	0.41	-156	3.50	-20	0.063	-78	0.33	101
4.6	0.40	-179	3.45	-38	0.068	-93	0.33	90
4.7	0.38	154	3.42	-61	0.072	-123	0.33	79
4.8	0.37	135	3.38	-77	0.075	-140	0.31	71
4.9	0.33	109	3.34	-101	0.078	-167	0.25	51
5.0	0.29	89	3.27	-122	0.079	172	0.17	22